

Complete if Known	
Application Number	10/686,795
Filing Date	October 16, 2003
First Named Inventor	Joseph J. Sumakeris
Group Art Unit	2811
Examiner Name	Cuong Quang Nguyen
Attorney Docket Number	5308-248

[illegible][illegible]

OTHER NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
es	4	Baranov et al., "EPR Study of Shallow and Deep Phosphorous Centers in 6H-SiC," Physical Review B66, 2002, pp. 165206-1 through 165206-7	
ca	5	Rashid et al., "Trench Oxide Protection for 10 kV 4H-SiC Trench MOSFETs," Power Electronics and Drive Systems, 2003, Vol. 2, pp. 1354-1358	
Oh	6	Sugawara et al., "12-19kV 4H-SiC pin Diodes with Low Power Loss," Proceedings of 2001 International Symposium on Power Semiconductor Devices & Ics, Osaka, pp. 27-30	
Ch	7	Notification of Transmittal of the International Search Report and the Written Opinion of the International Searching Authority, or the Declaration, PCT/US2004/031883, January 7, 2005	

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

AUG 30 2004

Sheet

D1

of

D1

Application Number

10/686.795

Filing Date

October 16, 2003

First Named Inventor

Joseph John Sumakeris

Group Art Uni

2811

Examiner Name

Cuong Q. Nguyen

Attorney Docket Number

5308-286

[illegible]

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T
		Office	Number	Kind Code (if known)			

[illegible]

considered, whether
sidered. Include c

Date Considered

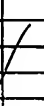
3-16-05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

10-16-03

Substitute form 1449A/PTO		Complete if Known 10/686795	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	To Be Assigned
		Filing Date	Concurrently Herewith
		First Named Inventor	Joseph John Sumakeris
		Group Art Unit	
		Examiner Name	
Sheet 1 of 1	Attorney Docket Number	5308-2861	

U.S. PATENTS AND PATENT PUBLICATIONS					
Examiner Initials*	Cite No.	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code (if known)		
Ch	1	US-6,472,677	B1	Rodriguez et al.	10-29-2002
Ch	2	US-6,403,982	B2	Carter, Jr. et al.	06-11-2002
Ch	3	US-6,396,080	B2	Carter, Jr. et al.	05-28-2002
Ch	4	US-6,391,690	B2	Miyasaka	05-21-2002
Ch	5	US-6,359,309	B1	Liao et al.	03-19-2002
Ch	6	US 2001/0017374	A1	Carter, Jr. et al.	08-30-2001
Ch	7	US-6,222,229	B1	Hebert et al.	04-24-2001
Ch	8	US-6,218,680	B1	Carter, Jr. et al.	04-17-2001
Ch	9	US-6,215,152	B1	Hebert	04-10-2001
Ch	10	US-6,190,970	B1	Liao et al.	02-20-2001
Ch	11	US-6,114,225		Liao et al.	09-05-2000
Ch	12	US-6,100,168		Liao et al.	08-08-2000
Ch	13	US-5,972,801		Lipkin et al.	10-26-1999
Ch	14	US-5,698,891		Tomita et al.	12-16-1997
Ch	15	US-5,506,421		Palmour	04-09-1996
Ch	16	US-RE.34,861		Davis et al.	02-14-1995
Ch	17	US-5,296,258		Tay et al.	03-22-1994
Ch	18	US-5,164,359		Calviello et al.	11-17-1992
Ch	19	US-5,160,696		Bowman	11-03-1992
Ch	20	US-4,866,005		Davis et al.	09-12-1989
Ch	21	US-4,766,482		Smeltzer et al.	08-23-1988
Ch	22	US-4,260,448		Herzer	04-07-1981
		US-			
		US-			
		US-			
		US-			

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No.	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T
		Office	Number	Kind Code (if known)			
							

OTHER NON PATENT LITERATURE DOCUMENTS				
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published		T
Ch	23	Heissenstein et al., "Characterization of phosphorus doped <i>n</i> -type 6 <i>H</i> -silicon carbide epitaxial layers produced by nuclear transmutation doping," Journal of Applied Physics, Volume 83, Number 12, pp. 7542-7546, 15 June 1998		

Examiner Signature	<i>Ch</i>	Date Considered	03-16-05
--------------------	-----------	-----------------	----------

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.